ON Semiconductor®



Title of Change:	Wafer Fab Capacity Expansion for Trench 6 MOSFET Technology at Global Foundries in New York, US.		
Proposed First Ship date:	04 Feb 2021 or earlier if approved by customer		
Contact Information:	Contact your local ON Semiconductor Sales Office or MohdHezri.AbuBakar@onsemi.com		
PCN Samples Contact:	Contact your local ON Semiconductor Sales Office or < <u>PCN.samples@onsemi.com</u> >. Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change. Samples delivery timing will be subject to request date, sample quantity and special customer packing/label requirements.		
Additional Reliability Data:	Contact your local ON Semico	onductor Sales Offic	e or <u>Robert.Baran@onsemi.com</u>
Type of Notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <u>PCN.Support@onsemi.com</u>		
Marking of Parts/ Traceability of Change:	Material will be traceable with ONs lot trace code & tracking		
Change Category:	Wafer Fab Change		
Change Sub-Category(s):	Manufacturing Site Addition		
Sites Affected:	·		
DN Semiconductor Sites External Foundry/Subcon Sites			ry/Subcon Sites
None		Global Foundries East Fishkill, New York, United States	
Description and Purpose:			
addition of the Global Foundries Fab loo	cated in New York, US, for the m as an additional site for wafer fa 200mm wafers.	nanufacturing of the	MOSFET technology products, is announcing the ese products. and and back metal, utilizing 300mm diameter wafer
There is no product marking change as			
	Before Change Desci	ription	After Change Description
Wafer Fabrication Site	ON Aizu, Japan ON Gresham, US		ON Aizu, Japan ON Gresham, US <u>Global Foundries, US</u>
Wafer Diameter	200mm (existing si	ites)	300mm (Global Foundries)
Wafer Probe Site	ON Seremban, Mala ON Bucheon, Kor	,	ON Seremban, Malaysia ON Bucheon, Korea <u>Global Foundries, US</u>
	ON ISMF, Malays	sia	ON ISMF, Malaysia

ON Bucheon, Korea

Back Grind, Back Metal Site

ON Bucheon, Korea Global Foundries, US



Reliability Data Summary:

QV DEVICE NAME: NVMFS5C404NLT1G RMS: 66099, 67744, 67566, 67986 PACKAGE: SO8FL-HE

Test	Specification	Condition	Interval	Result
HTRB	JESD22-A108	Ta=175°C, 100% max rated Vds	1008 hrs	0/231
HTGB	JESD22-A108	Ta=175°C, 100% max rated Vgss	1008 hrs	0/231
HTSL	JESD22-A103	Ta= 175°C	1008 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off =2 min	15000 cyc	0/231
тс	JESD22-A104	Ta= -55°C to +150°C	1000 сус	0/231
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/231
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/231
PC	J-STD-020 JESD-A113	MSL1 @ 260°C		

QV DEVICE NAME: NVMFS5C410NLT1G RMS: 66101, 67567 PACKAGE: SO8FL

Test	Specification	Condition	Interval	Result
HTRB	JESD22-A108	Ta=175°C, 100% max rated Vds	1008 hrs	0/231
HTGB	JESD22-A108	Ta=175°C, 100% max rated Vgss	1008 hrs	0/231
HTSL	JESD22-A103	Ta= 175°C	2016 hrs	0/231
IOL	MIL-STD-750 (M1037) AEC-Q101	Ta=+25°C, delta Tj=100°C On/off =2 min	15000 cyc	0/231
тс	JESD22-A104	Ta= -55°C to +150°C	1000 сус	0/231
HAST	JESD22-A110	130°C, 85% RH, 18.8psig, bias	96 hrs	0/231
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig, unbiased	96 hrs	0/231
PC	J-STD-020 JESD-A113	MSL1 @ 260°C		

QV DEVICE NAME: NVMFS5C404NT1G RMS: 66100 PACKAGE: S08FL-HE

Test	Specification	Condition	Interval	Result
HTGB	JESD22-A108	Ta=175°C, 100% max rated Vgss	1008 hrs	0/231

ON Semiconductor®



Electrical Characteristics Summary:

Electrical characteristics are not impacted.

List of Affected Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the **PCN Customized Portal**.

Part Number	Qualification Vehicle
NTMFS5C410NT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G, NVMFS5C404NT1G
NTMFS5C410NT3G	NVMFS5C410NLT1G, NVMFS5C404NLT1G, NVMFS5C404NT1G
NTMFS5C426NT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G, NVMFS5C404NT1G
NTMFS5C442NLT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G
NTMFS5C460NLT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G
NTMFS5C450NLT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G
NTMFS5C442NT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G, NVMFS5C404NT1G
NTMFS5C456NLT1G	NVMFS5C410NLT1G, NVMFS5C404NLT1G
NTMFS5C460NLT3G	NVMFS5C410NLT1G, NVMFS5C404NLT1G